

**SOT-23**

**Pin Definition:**

1. Gate
2. Source
3. Drain

**PRODUCT SUMMARY**

<b>V<sub>DS</sub> (V)</b>	<b>R<sub>DS(on)</sub>(Ω)(max)</b>	<b>I<sub>D</sub> (A)</b>
600	700 @ V <sub>GS</sub> = 0V	0.03

**Features**

- Depletion Mode
- Low Gate Charge

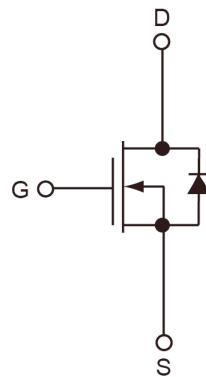
**Application**

- Converters
- Telecom

**Ordering Information**

<b>Part No.</b>	<b>Package</b>	<b>Packing</b>
TSM126CX RFG	SOT-23	3kpcs / 7" Reel

**Note:** "G" denotes Halogen Free Product.

**Block Diagram**

**N-Channel MOSFET**
**Absolute Maximum Ratings (Ta = 25°C unless otherwise noted)**

<b>Parameter</b>	<b>Symbol</b>	<b>Limit</b>	<b>Unit</b>
Drain-Source Voltage	V <sub>DS</sub>	600	V
Gate-Source Voltage	V <sub>GS</sub>	±20	V
Continuous Drain Current	T <sub>c</sub> =25°C	I <sub>D</sub>	A
Continuous Drain Current		0.030	A
Pulsed Drain Current <sup>a</sup>	I <sub>DM</sub>	0.024	A
Maximum Power Dissipation	P <sub>D</sub>	0.120	W
Soldering Temperature <sup>b</sup>	T <sub>L</sub>	300	°C
Operating Junction Temperature	T <sub>J</sub>	+150	°C
Operating Junction and Storage Temperature Range	T <sub>J</sub> , T <sub>STG</sub>	-55 to +150	°C

**Thermal Performance**

<b>Parameter</b>	<b>Symbol</b>	<b>Limit</b>	<b>Unit</b>
Thermal Resistance, Junction to Ambient	R <sub>θ<sub>JA</sub></sub>	250	°C/W

**Notes:**

- a. Pulse width limited by the Maximum junction temperature
- b. Distance of 1.6mm from case for 10 seconds.

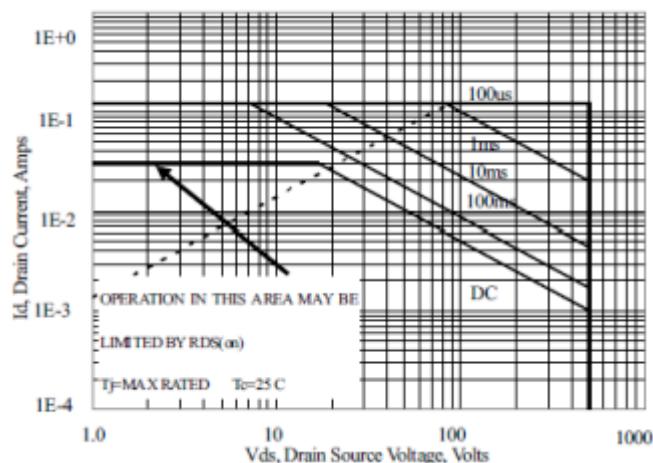
**Electrical Specifications** ( $T_j = 25^\circ\text{C}$  unless otherwise noted)

Parameter	Conditions	Symbol	Min	Typ	Max	Unit
<b>Static<sup>a</sup></b>						
Drain-Source Breakdown Voltage	$V_{GS} = -5\text{V}$ , $I_D = 250\mu\text{A}$	$BV_{DSS}$	600	--	--	V
Gate Threshold Voltage	$V_{DS} = 3\text{V}$ , $I_D = 8\mu\text{A}$	$V_{GS(TH)}$	-2.7	-1.8	-1.0	V
Drain-Source cutoff current	$V_{DS} = 600\text{V}$ , $V_{GS} = -5\text{V}$ , $T_a = 25^\circ\text{C}$	$I_{DS(OFF)}$	--	--	0.1	$\mu\text{A}$
Drain-Source cutoff current	$V_{DS} = 480\text{V}$ , $V_{GS} = -5\text{V}$ , $T_a = 125^\circ\text{C}$				10	$\mu\text{A}$
Gate-Source Leakage Current	$V_{GS} = \pm 20\text{V}$ , $V_{DS} = 0\text{V}$	$I_{GSS}$	--	--	$\pm 10$	$\mu\text{A}$
On-state Drain Current	$V_{DS} = 25\text{V}$ , $V_{GS} = 0\text{V}$	$I_{DSS}$	12	--	--	mA
Drain-Source On-State Resistance	$V_{GS} = 0\text{V}$ , $I_D = 3\text{mA}$	$R_{DS(ON)}$	--	350	700	$\Omega$
	$V_{GS} = 10\text{V}$ , $I_D = 16\text{mA}$			400	800	$\Omega$
Forward Transconductance	$ V_{DS}  > 2 I_D * R_{DS(ON)max}$ , $I_D = 0.01\text{A}$	$g_{fs}$	0.008	0.017	--	S
<b>Dynamic</b>						
Input Capacitance	$V_{DS} = 25\text{V}$ , $V_{GS} = -5\text{V}$ , $f = 1.0\text{MHz}$	$C_{iss}$	--	51.42	--	pF
Output Capacitance		$C_{oss}$	--	4.48	--	
Reverse Transfer Capacitance		$C_{rss}$	--	1.12	--	
Total Gate Charge	$V_{DS} = 400\text{V}$ , $I_D = 0.01\text{A}$ , $V_{GS} = -5\text{V}$ to $5\text{V}$	$Q_g$	--	1.18	--	nC
Gate-Source Charge		$Q_{gs}$	--	0.49	--	
Gate-Drain Charge		$Q_{gd}$	--	0.365	--	
<b>Switching</b>						
Turn-On Delay Time	$V_{DD} = 300\text{V}$ , $I_D = 0.01\text{A}$ , $V_{GS} = -5\text{V}$ to $7\text{V}$ , $R_G = 6\Omega$	$t_{d(on)}$	--	10.01	--	ns
Turn-On Rise Time		$t_r$	--	55.7	--	
Turn-Off Delay Time		$t_{d(off)}$	--	57.2	--	
Turn-Off Fall Time		$t_f$	--	135.5	--	
<b>Source-Drain Diode</b>						
Diode forward Current	Continuous	$I_S$	--	--	0.025	A
Diode Pulse Current		$I_{SM}$	--	--	0.100	A
Diode Forward Voltage	$I_{SD} = 16\text{mA}$ , $V_{GS} = -5\text{V}$	$V_{SD}$	--	--	1.2	V
Reverse Recovery Time	$I_F = 0.01\text{A}$ , $V_{GS} = -10\text{V}$ $dI_F/dt = 100\text{A}/\mu\text{s}$ , $V_R = 30\text{V}$	$t_{rr}$	--	243.1	--	ns
Reverse Recovery Charge		$Q_{rr}$	--	639	--	nC

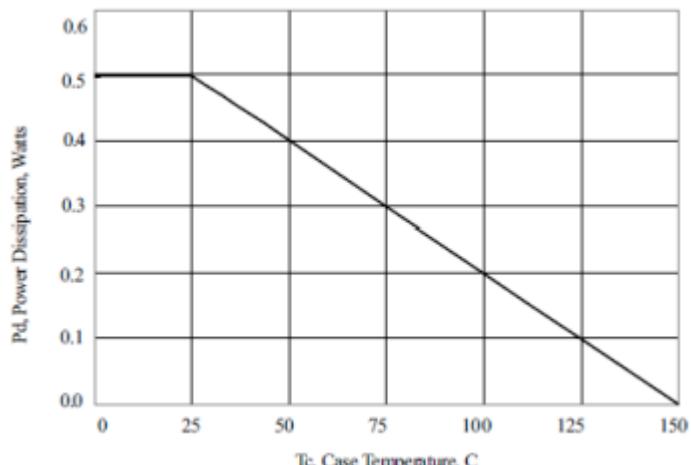
**Notes:**a. pulse test:  $PW < 380\mu\text{s}$ , duty cycle  $< 2\%$

**Electrical Characteristics Curves** ( $T_a = 25^\circ\text{C}$ , unless otherwise noted)

**Maximum Forward Bias Safe Operation Area**

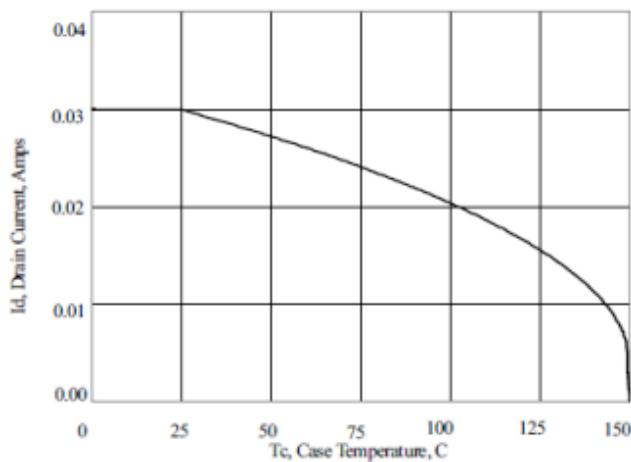


**Maximum Power Dissipation vs. Case Temperature**

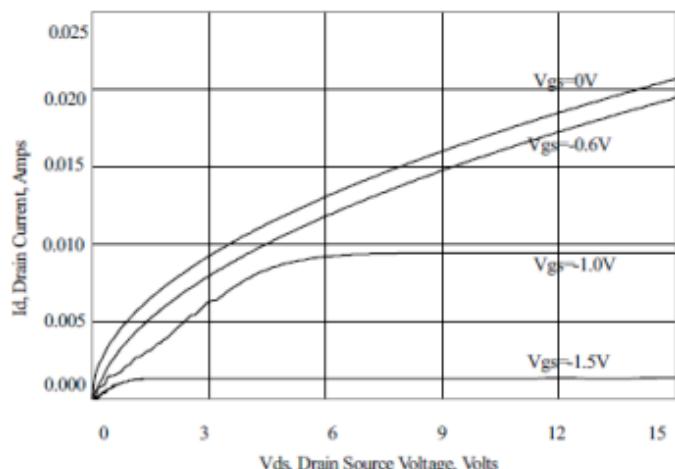


**Maximum Continuous Drain Current vs.**

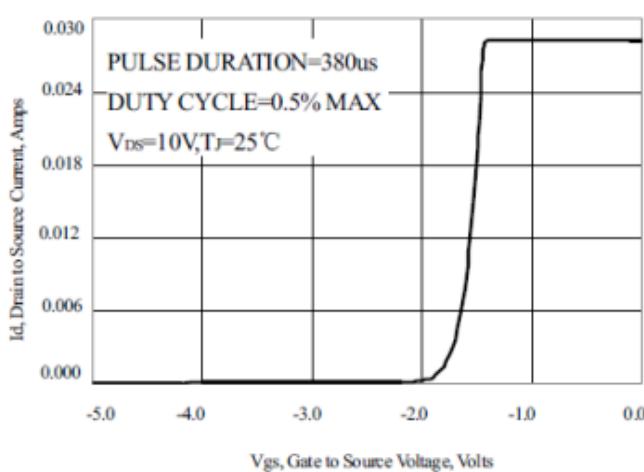
**Case Temperature**



**Typical Output Characteristics**

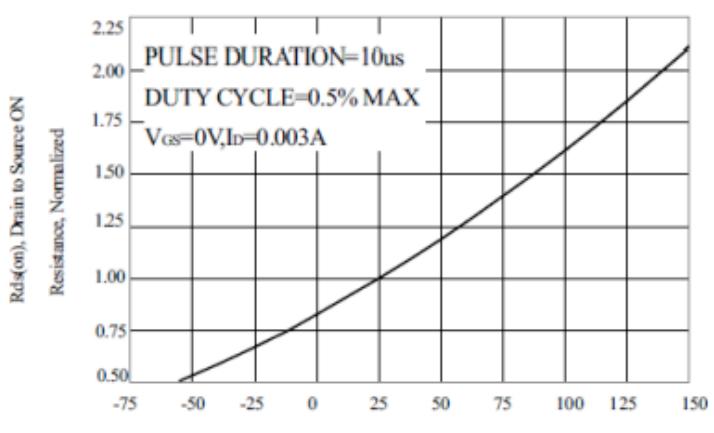


**Typical Transfer Characteristics**



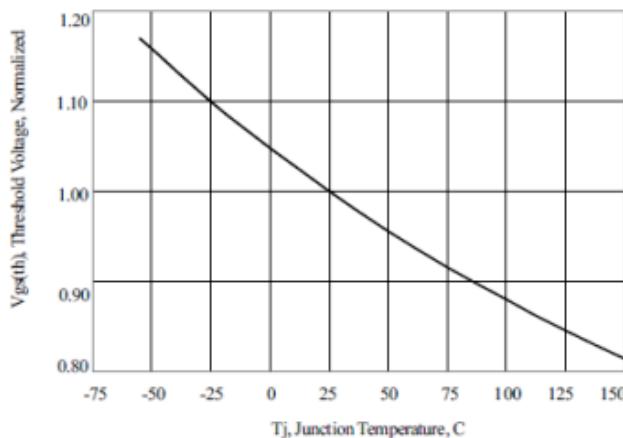
**Drain to Source ON Resistance**

**vs. Junction Temperature**

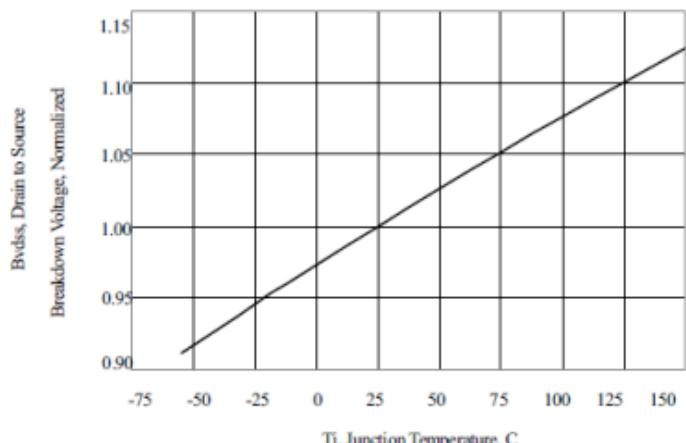


**Electrical Characteristics Curves** ( $T_a = 25^\circ\text{C}$ , unless otherwise noted)

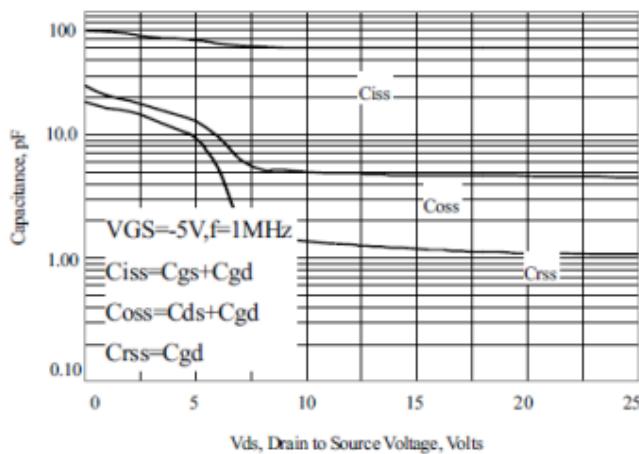
**Threshold Voltage vs. Junction Temperature**



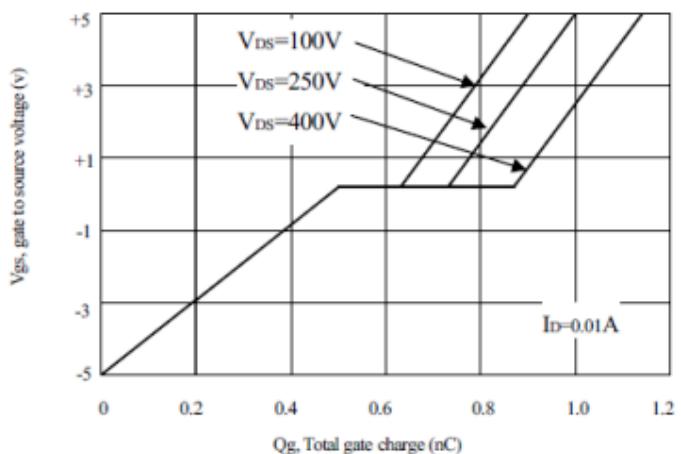
**Breakdown Voltage vs. Junction Temperature**



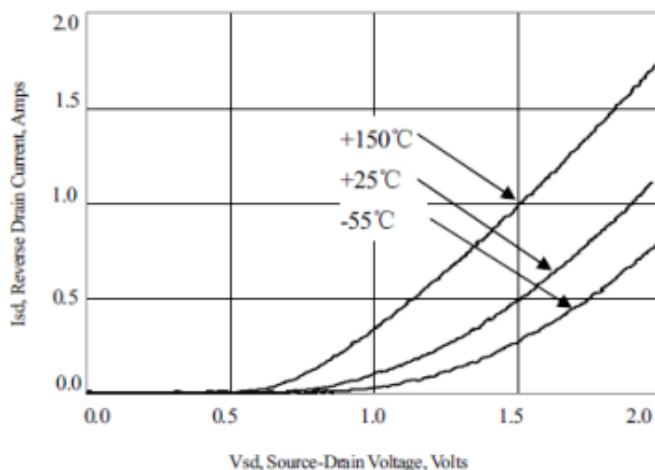
**Typical Capacitance vs. Drain to source Voltage**



**Typical Gate Charge vs. Gate to Source Voltage**

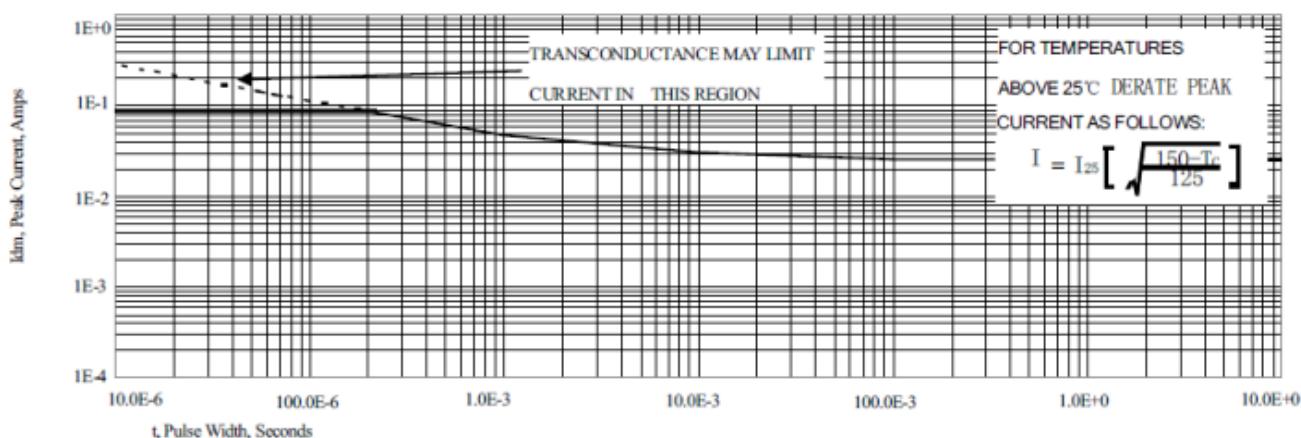


**Typical Body Diode Transfer Characteristics**

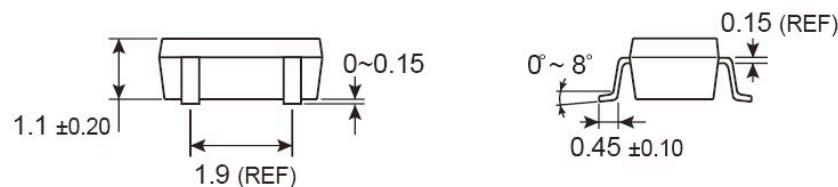
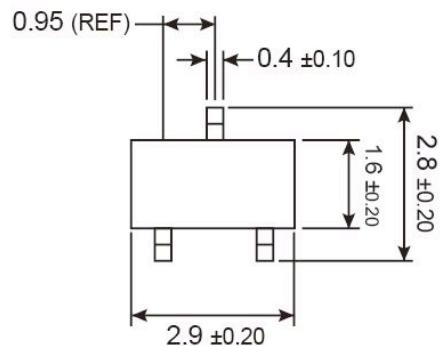


**Electrical Characteristics Curves** ( $T_a = 25^\circ\text{C}$ , unless otherwise noted)

**Maximum Peak Current Capability**



### SOT-23 Mechanical Drawing



Unit: Millimeters

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